

Final Product/Process Change Notification

Document # : FPCN20579XA Issue Date: 28 June 2016

Title of Change:	The addition of ASMC (Shanghai, China) and LiON Microelectronics (Hang Zhou, China) as qualified wafer foundry facilities for ON Semiconductor Zener Products.		
Proposed first ship date:	7 Oct 2016		
Contact information:	Contact your local ON Semiconductor Sales Office or <eben.lim@onsemi.com></eben.lim@onsemi.com>		
Samples:	Contact your local ON Semiconductor Sales Office or <eben.lim@onsemi.com></eben.lim@onsemi.com>		
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or <nicky.siu@onsemi.com></nicky.siu@onsemi.com>		
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <pcn.support@onsemi.com>.</pcn.support@onsemi.com>		
Change Part Identification:	Unless with customer approval (OA), the affected devices from ON Semiconductor with date code Oct 2016 and greater may be sourced from either ASMC, Shanghai or Hang Zhou LiON (Back Metallization) or the ON Semiconductor ISMF Fab, Seremban.		
Change category:	✓ Wafer Fab Change ✓ Assembly Change ✓ Test Change ✓ Other		
Change Sub-Category(s): Manufacturing Site Change/ Manufacturing Process Chan	Shipping/ Packaging/ Marking		
Sites Affected: All site(s) not ap	oplicable ON Semiconductor site(s): External Foundry/Subcon site(s) ADVANCED SEMICONDUCTOR MANUFACTURING CORP LTD HANGZHOU LION MICROELECTRONICS CO LTD		

Description and Purpose:

ON Semiconductor is notifying customers of the qualification of ASMC (Advanced Semiconductor Manufacturing Corporation Limited in Shanghai, China) and LiON Microelectronics Corporation Limited in Hang Zhou, China, as second source foundry facilities to the current ON Semiconductor ISMF fabrication facility in Seremban, Malaysia for Zener products.

Prior to this qualification, the ASMC and LiON facilities have been supplying wafers to ON Semiconductor. ASMC and LiON are external foundry facilities that are ISO/TS16949 and ISO 9001 certified.

The ASMC and ISMF fabrication facilities have standardized wafer process flows that are compatible in order to meet ON Semiconductor quality requirements.

Qualification tests are designed to show that the reliability of the transferred devices will continue to meet or exceed ON Semiconductor standards.

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Reliability Data Summary:

MMBZ33VALT1G

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108 Ta=_150°C, 80% max rated V		1008hrs	0/252
TC+PC	JESD22-A104	Ta= -65°C to +150°C	1000 сус	0/252
HAST+ PC	JESD22-A110	130°C, 85% RH, 18.8psig, bias	192 hrs	0/246
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs	0/252
PC	J-STD-020 JESD-A113	MSL 1 @ 260 ℃		
RSH	JESD22- B106	Ta = 265C, 10 sec		0/90

MMBZ47VALT1G

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta=_150°C, 80% max rated V	1008hrs	0/252
HAST+ PC	JESD22-A110	130°C, 85% RH, 18.8psig, bias	192 hrs	0/240

Electrical Characteristic Summary:

Three temperature characterization and ESD performance meet datasheet specification. Detail of Electrical characterization result is available upon request.

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Part Number	Qualification Vehicle
DF6A6.8FUT1G	MMBZ47VALT1G
ESD7124MUTBG	MMBZ47VALT1G
ESD9X12ST5G	MMBZ47VALT1G
ESD9X3.3ST5G	MMBZ47VALT1G
ESD9X5.0ST5G	MMBZ47VALT1G
MMBZ12VALT1G	MMBZ47VALT1G
MMBZ15VALT1G	MMBZ47VALT1G
MMBZ16VALT1G	MMBZ47VALT1G
MMBZ16VTALT1G	MMBZ47VALT1G
MMBZ18VALT1G	MMBZ47VALT1G
MMBZ20VALT1G	MMBZ47VALT1G
MMBZ20VAWT1G	MMBZ47VALT1G
MMBZ27VALT1G	MMBZ47VALT1G
MMBZ27VALT3G	MMBZ47VALT1G
MMBZ27VAWT1G	MMBZ47VALT1G
MMBZ33VALT1G	MMBZ47VALT1G
MMBZ33VAWT1G	MMBZ47VALT1G
MMBZ47VALT1G	MMBZ47VALT1G MMBZ47VALT1G
MMBZ5V6ALT1G	MMBZ47VALTIG
MMBZ5V6ALTIG	MMBZ47VALTIG
MMBZ6V2ALT1G	
	MMBZ47VALT1G
MMBZ6V8ALT1G	MMBZ47VALT1G
MMQA12VT1G	MMBZ47VALT1G
MMQA20VT1G	MMBZ47VALT1G
MMQA33VT1G	MMBZ47VALT1G
MMQA5V6T1G	MMBZ47VALT1G
MMQA5V6T3G	MMBZ47VALT1G
MMQA6V8T1G	MMBZ47VALT1G
MSQA6V1W5T2G	MMBZ47VALT1G
NSQA6V8AW5T2G	MMBZ47VALT1G
NUP4060AXV6T1G	MMBZ47VALT1G
NUP8011MUTAG	MMBZ47VALT1G
NZ23C5V6ALT1G	MMBZ47VALT1G
NZL5V6AXV3T1G	MMBZ47VALT1G
NZL7V5AXV3T1G	MMBZ47VALT1G
NZQA5V6AXV5T1G	MMBZ47VALT1G
NZQA6V8AXV5T1G	MMBZ47VALT1G
SD05T1G	MMBZ47VALT1G
SD05T3G	MMBZ47VALT1G
SD12T1G	MMBZ47VALT1G
SM05T1G	MMBZ47VALT1G
SM12T1G	MMBZ47VALT1G
SMF05CT1G	MMBZ47VALT1G
SMF05CT2G	MMBZ47VALT1G
UESD3.3DT5G	MMBZ47VALT1G
UESD5.0DT5G	MMBZ47VALT1G
UESD6.0DT5G	MMBZ47VALT1G

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